

# 8-Bit Static Shift Register MC14014B, MC14021B

The MC14014B and MC14021B 8-Bit static shift registers are constructed with MOS P-channel and N-channel enhancement mode devices in a single monolithic structure. These shift registers find primary use in parallel-to-serial data conversion, synchronous and asynchronous parallel input, serial output data queueing; and other general purpose register applications requiring low power and/or high noise immunity.

#### **Features**

- Synchronous Parallel Input/Serial Output (MC14014B)
- Asynchronous Parallel Input/Serial Output (MC14021B)
- Synchronous Serial Input/Serial Output
- Full Static Operation
- "Q" Outputs from Sixth, Seventh, and Eighth Stages
- Double Diode Input Protection
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range
- MC14014B Pin-for-Pin Replacement for CD4014B
- MC14021B Pin-for-Pin Replacement for CD4021B
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- This Device is Pb-Free and is RoHS Compliant

## MAXIMUM RATINGS (Voltages Referenced to VSS)

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8-Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Package: -7.0 mW/°C From 65 °C To 125 °C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

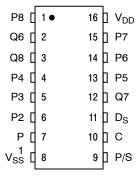
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

1

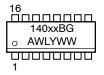


SOIC-16 D SUFFIX CASE 751B

## **PIN ASSIGNMENT**



### **MARKING DIAGRAM**



xx = Specific Device Code A = Assembly Location

WL, L = Wafer Lot
 YY, Y = Year
 WW, W = Work Week
 G = Pb-Free Indicator

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

**TRUTH TABLE** 

## **SERIAL OPERATION:**

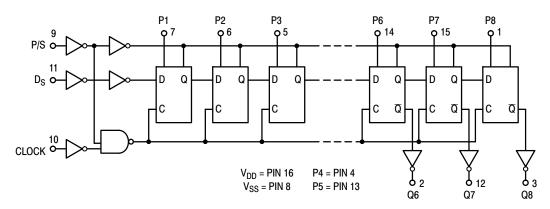
				Q6	Q7	Q8
t	Clock	Ds	P/S	t=n+6	t=n+7	t=n+8
n	\	0	0	0	?	?
n+1	_	1	0	1	0	?
n+2		0	0	0	1	0
n+3		1	0	1	0	1
	\	Х	0	Q6	Q7	Q8

## **PARALLEL OPERATION:**

CI					
MC14014B	MC14021B	Ds	P/S	Pn	*Q <sub>n</sub>
	Х	Х	1	0	0
	Х	Х	1	1	1

\*Q6, Q7, & Q8 are available externally X = Don't Care

## **LOGIC DIAGRAM**



## **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				-55	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
$V_{in} = 0 \text{ or } V_{DD}$	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95		4.95 9.95 14.95	5.0 10 15		4.95 9.95 14.95	- - -	Vdc
Input Voltage $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11		3.5 7.0 11	2.75 5.50 8.25	1 1 1	3.5 7.0 11	- - -	Vdc
Output Drive Current $ \begin{aligned} &(V_{OH}=2.5 \text{ Vdc})\\ &(V_{OH}=4.6 \text{ Vdc})\\ &(V_{OH}=9.5 \text{ Vdc})\\ &(V_{OH}=13.5 \text{ Vdc}) \end{aligned} $	Source	I <sub>OH</sub>	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	1 1 1	-1.7 -0.36 -0.9 -2.4	- - -	mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		l <sub>in</sub>	15	_	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	-	-	-	_	5.0	7.5	-	-	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	5.0 10 15	- - -	0.005 0.010 0.015	5.0 10 15	- - -	150 300 600	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C <sub>L</sub> = 50 pF on all outp buffers switching)	ent,	lτ	5.0 10 15			$I_T = (1$	.75 μΑ/kHz) .50 μΑ/kHz) .25 μΑ/kHz)	f + I <sub>DD</sub>		,	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.0015.

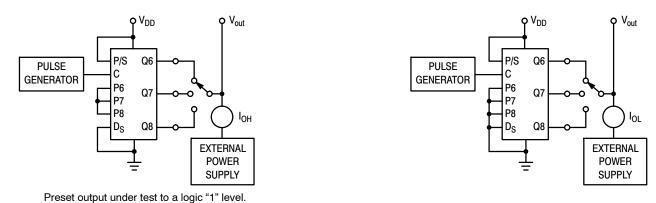
Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
 The formulas given are for the typical characteristics only at 25 °C.

<sup>4.</sup> To calculate total supply current at loads other than 50 pF:

## SWITCHING CHARACTERISTICS (Note 5) ( $C_L$ = 50 pF, $T_A$ = 25 $^{\circ}C$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise and Fall Time  t <sub>TLH</sub> , t <sub>THL</sub> = (1.5 ns/pF) C <sub>L</sub> + 25 ns  t <sub>TLH</sub> , t <sub>THL</sub> = (0.75 ns/pF) C <sub>L</sub> + 12.5 ns	t <sub>TLH</sub> , t <sub>THL</sub>	5.0 10	- -	100 50	200 100	ns
t <sub>TLH</sub> , t <sub>THL</sub> = (0.55 ns/pF) C <sub>L</sub> + 9.5 ns		15	_	40	80	
Propagation Delay Time (Clock to Q, P/S to Q)	t <sub>PLH</sub> ,					ns
$t_{PHL}$ , $t_{PLH}$ = (1.7 ns/pF) $C_L$ + 315 ns $t_{PHL}$ , $t_{PLH}$ = (0.66 ns/pF) $C_L$ + 137 ns	t <sub>PHL</sub>	5.0 10		400 170	800 340	
$t_{PHL}$ , $t_{PLH} = (0.00 \text{ ns/pF}) C_L + 137 \text{ ns}$ $t_{PHL}$ , $t_{PLH} = (0.5 \text{ ns/pF}) C_L + 90 \text{ ns}$		15	_	115	230	
Clock Pulse Width	t <sub>WH</sub>	5.0	400	150	-	ns
		10	175	75	_	
		15	135	40		
Clock Frequency	f <sub>cl</sub>	5.0	_	3.0	1.5	MHz
		10		6.0	3.0	
		15		8.0	4.0	
Parallel/Serial Control Pulse Width	t <sub>WH</sub>	5.0	400	150	_	ns
		10 15	175 135	75 40	_	
	_	+				
Setup Time	t <sub>su</sub>	5.0	200	100	_	ns
P/S to Clock		10 15	100 80	50 40	_	
Hold Time	t <sub>h</sub>	5.0	20	- 2.5	_	ns
Clock to P/S		10	20	- 10	_ _	
		15	25	0	_	
Setup Time	t <sub>su</sub>	5.0	350	150	-	ns
Data (Parallel or Serial) to		10	80	50		
Clock or P/S		15	60	30	_	
Hold Time	t <sub>h</sub>	5.0	45	0	-	ns
Clock to D <sub>s</sub>		10	35	0	_	
		15	35	5	_	
Hold Time	t <sub>h</sub>	5.0	50	25	-	ns
Clock to P <sub>n</sub>		10	45	20		
		15	45	20		
Input Clock Rise Time	t <sub>r(cl)</sub>	5.0	_	-	15	μs
		10	_	_	5	
		15			4	

<sup>5.</sup> The formulas given are for the typical characteristics only at 25 °C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.



**Figure 1. Output Source Current Test Circuit** 

Figure 2. Output Sink Current Test Circuit

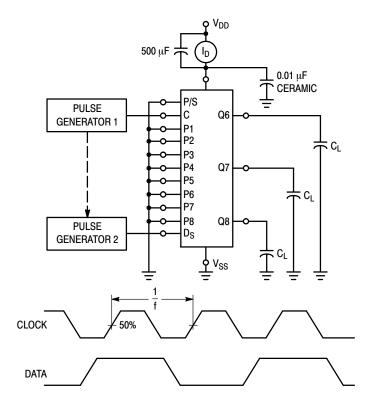


Figure 3. Power Dissipation Test Circuit and Waveform

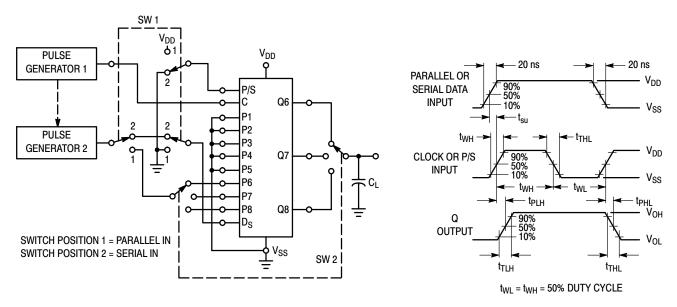


Figure 4. Switching Time Test Circuit and Waveforms

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14014BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14014BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14014BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC14021BDG	SOIC-16 (Pb-Free)	48 Units / Rail
MC14021BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14021BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

## **REVISION HISTORY**

Revision	Description of Changes	Date
10	Rebranded the Data Sheet to <b>onsemi</b> format	7/11/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.



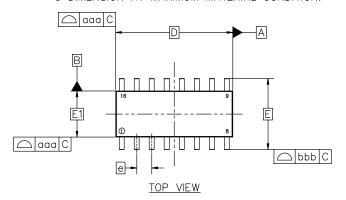


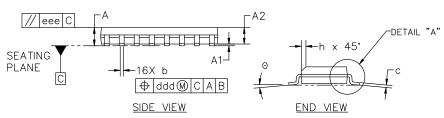
## SOIC-16 9.90x3.90x1.37 1.27P CASE 751B ISSUE M

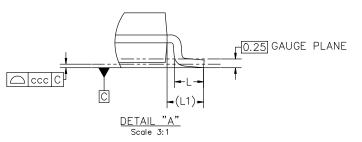
**DATE 18 OCT 2024** 

### NOTES:

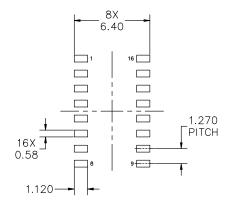
- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. DIMENSION IN MILLIMETERS. ANGLE IN DEGREES.
- 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15mm PER SIDE.
- 5. DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127mm TOTAL IN EXCESS OF THE 6 DIMENSION AT MAXIMUM MATERIAL CONDITION.







MILLIMETERS						
DIM	MIN	NOM	MAX			
А	1.35	1.55	1.75			
A1	0.10	0.18	0.25			
A2	1.25	1.37	1.50			
b	0.35	0.42	0.49			
С	0.19	0.22	0.25			
D		9.90 BSC				
E		6.00 BSC				
E1	3.90 BSC					
е		1.27 BSC				
h	0.25		0.50			
L	0.40	0.83	1.25			
L1		1.05 REF				
Θ	0.		7*			
TOLERAN	CE OF FC	RM AND	POSITION			
aaa	0.10					
bbb	0.20					
ccc	0.10					
ddd		0.25				
eee		0.10				



### RECOMMENDED MOUNTING FOOTPRINT

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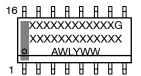
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## **SOIC-16 9.90x3.90x1.37 1.27P** CASE 751B

ISSUE M

**DATE 18 OCT 2024** 

## GENERIC MARKING DIAGRAM\*



XXXXX = Specific Device Code

A = Assembly Location
WL = Wafer Lot

Y = Year
WW = Work Week
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:		STYLE 2:		STYLE 3:	S	TYLE 4:	
	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE #1
	BASE	2.	ANODE	2.	BASE. #1	2.	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER. #1	3.	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	
	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	
13.	BASE	13.		13.	COLLECTOR, #4	13.	BASE, #2
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1
STYLE 5:		STYLE 6:		STYLE 7:			
PIN 1.	DRAIN, DYE #1	PIN 1.	CATHODE	PIN 1.	SOURCE N-CH		
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPUT)		
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPUT)		
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH		
5.	DRAIN, #3	5.		5.	COMMON DRAIN (OUTPUT)		
6.	DRAIN, #3	6.		6.	COMMON DRAIN (OUTPUT)		
7.	DRAIN, #4		CATHODE	7.	COMMON DRAIN (OUTPUT)		
8.	DRAIN, #4		CATHODE	8.	SOURCE P-CH		
9.	GATE, #4		ANODE	9.	SOURCE P-CH		
10.	SOURCE, #4	10	ANODE	10.	COMMON DRAIN (OUTPUT)		
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPUT)		
12.	GATE, #3 SOURCE, #3	11. 12.	ANODE ANODE	11. 12.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
12. 13.	GATE, #3 SOURCE, #3 GATE, #2	11. 12. 13.	ANODE ANODE ANODE	11. 12. 13.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH		
12. 13. 14.	GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2	11. 12. 13. 14.	ANODE ANODE ANODE ANODE	11. 12. 13. 14.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		
12. 13. 14. 15.	GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2 GATE, #1	11. 12. 13. 14. 15.	ANODE ANODE ANODE ANODE ANODE	11. 12. 13. 14. 15.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT)		
12. 13. 14.	GATE, #3 SOURCE, #3 GATE, #2 SOURCE, #2	11. 12. 13. 14.	ANODE ANODE ANODE ANODE	11. 12. 13. 14.	COMMON DRAIN (OUTPUT) COMMON DRAIN (OUTPUT) GATE N-CH COMMON DRAIN (OUTPUT)		

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